Stefano Ossicini

List of Publications by Year
in descending order

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185 papers	6,729 citations	87723 38 h-index	69108 77 g-index
193 all docs	193 docs citations	193 times ranked	5022 citing authors

#	Article	IF	Citations
1	(Invited) Electronic and Optical Properties of Si, Ge and Sige Low Dimensional Systems: Ab-Initio Results. ECS Meeting Abstracts, 2021, MA2021-01, 912-912.	0.0	0
2	Multiple exciton generation in isolated and interacting silicon nanocrystals. Nanoscale, 2021, 13, 12119-12142.	2.8	6
3	Ab initio studies of the optoelectronic structure of undoped and doped silicon nanocrystals and nanowires: the role of size, passivation, symmetry and phase. Faraday Discussions, 2020, 222, 217-239.	1.6	5
4	Surface chemistry effects on work function, ionization potential and electronic affinity of Si(100), Ge(100) surfaces and SiGe heterostructures. Physical Chemistry Chemical Physics, 2020, 22, 25593-25605.	1.3	7
5	Doping of IIIâ€“V Arsenide and Phosphide Wurtzite Semiconductors. Journal of Physical Chemistry C, 2020, 124, 27203-27212.	1.5	4
6	Preferential Positioning, Stability, and Segregation of Dopants in Hexagonal Si Nanowires. Nano Letters, 2019, 19, 866-876.	4.5	10
7	First Principles Modeling of Si/Ge Nanostructures for Photovoltaic and Optoelectronic Applications. Physica Status Solidi (B): Basic Research, 2018, 255, 1700627.	0.7	3
8	First Principle Studies of B and P Doped Si Nanocrystals. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700414.	0.8	9
9	First-principle investigations of carrier multiplication in Si nanocrystals: A short review. AIP Conference Proceedings, 2018, , .	0.3	0
10	Doped and codoped silicon nanocrystals: The role of surfaces and interfaces. Progress in Surface Science, 2017, 92, 375-408.	3.8	33
11	Tuning the Work Function of Si(100) Surface by Halogen Absorption: A DFT Study. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, .	0.8	19
12	Carrier Multiplication in Silicon Nanocrystals: Theoretical Methodologies and Role of the Passivation. Physica Status Solidi C: Current Topics in Solid State Physics, 2017, 14, 1700198.	0.8	5
13	Second Harmonic Generation in Silicon Based Heterostructures: The Role of Strain and Symmetry. Nanoscience and Nanotechnology Letters, 2017, 9, 1102-1107.	0.4	0
14	Work function bowing in Si1â^'xGex heterostructures: Ab initio results. Journal of Applied Physics, 2016, 119, .	1.1	7
15	First-principles calculations of electronic coupling effects in silicon nanocrystals: Influence on near band-edge states and on carrier multiplication processes. Solar Energy Materials and Solar Cells, 2016, 145, 162-169.	3.0	17
16	Strain-designed strategy to induce and enhance second-harmonic generation in centrosymmetric and noncentrosymmetric materials. Physical Review B, 2015, 92, .	1.1	10
17	Carrier multiplication in silicon nanocrystals: ab initio results. Beilstein Journal of Nanotechnology, 2015, 6, 343-352.	1.5	15
18	Energetics and carrier transport in doped Si/SiO₂quantum dots. Nanoscale, 2015, 7, 12564-12571.	2.8	13

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19	Ab initio energy loss spectra of Si and Ge nanowires. Physical Chemistry Chemical Physics, 2015, 17, 29085-29089.	1.3	3
20	Work Function Measurement of Silicon Germanium Heterostructures Combining Kelvin Force Microscopy and X-ray Photoelectron Emission Microscopy. Journal of Physical Chemistry C, 2015, 119, 26776-26782.	1.5	10
21	Understanding doping at the nanoscale: the case of codoped Si and Ge nanowires. Journal Physics D: Applied Physics, 2014, 47, 394013.	1.3	7
22	Conductance fluctuations in Si nanowires studied from first-principles. Journal of Applied Physics, 2014, 116, 074303.	1.1	6
23	Defects and strain enhancements of second-harmonic generation in Si/Ge superlattices. Journal of Chemical Physics, 2014, 140, 214705.	1.2	10
24	Siliconâ€“Germanium Nanowires: Chemistry and Physics in Play, from Basic Principles to Advanced Applications. Chemical Reviews, 2014, 114, 1371-1412.	23.0	151
25	Structural and electronic properties of Si1â^'xGex alloy nanowires. Journal of Applied Physics, 2014, 116, 154301.	1.1	11
26	Preferential Positioning of Dopants and Co-Dopants in Embedded and Freestanding Si Nanocrystals. Journal of the American Chemical Society, 2014, 136, 4404-4409.	6.6	66
27	Red-Shifted Carrier Multiplication Energy Threshold and Exciton Recycling Mechanisms in Strongly Interacting Silicon Nanocrystals. Journal of the American Chemical Society, 2014, 136, 13257-13266.	6.6	29
28	Determination of the Electronic Energy Levels of Colloidal Nanocrystals using Fieldâ€Effect Transistors and Abâ€Initio Calculations. Advanced Materials, 2014, 26, 5639-5645.	11.1	33
29	Silicon nanocrystals in carbide matrix. Solar Energy Materials and Solar Cells, 2014, 128, 138-149.	3.0	34
30	SiGe Nanowires for Thermoelectrics Applications. Lecture Notes in Nanoscale Science and Technology, 2014, , 497-515.	0.4	0
31	Silicon quantum dots embedded in a SiO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>matrix: From structural study to carrier transport properties. Physical Review B, 2013, 88, .	1.1	16
32	Optical absorption and emission of silicon nanocrystals: From single to collective response. Journal of Applied Physics, 2013, 113, 143505.	1.1	19
33	Role of strain in interacting silicon nanoclusters. Physical Review B, 2013, 87, .	1.1	13
34	Silicon nanocrystals from highâ€temperature annealing: Characterization on device level. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 669-675.	0.8	14
35	Ab Initio Electronic Gaps of Ge Nanodots: The Role of Self-Energy Effects. Journal of Physical Chemistry C, 2013, 117, 14229-14234.	1.5	12
36	Silicon-Based Light Sources. Series in Optics and Optoelectronics, 2013, , 333-438.	0.0	2

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37	Silicon Nanoscale Materials: From Theoretical Simulations to Photonic Applications. International Journal of Photoenergy, 2012, 2012, 1-21.	1.4	21
38	Photonic Properties of Silicon-Based Materials. International Journal of Photoenergy, 2012, 2012, 1-2.	1.4	1
39	Large crystal local-field effects in second-harmonic generation of a Si/CaF<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>interface: Anab initiostudy. Physical Review B, 2012, 86, .	1.1	6
40	Electron Transport in SiGe Alloy Nanowires in the Ballistic Regime from First-Principles. Nano Letters, 2012, 12, 2717-2721.	4.5	20
41	Doping of SiGe core-shell nanowires. Journal of Computational Electronics, 2012, 11, 272-279.	1.3	8
42	Carrier multiplication between interacting nanocrystals for fostering silicon-based photovoltaics. Nature Photonics, 2012, 6, 672-679.	15.6	111
43	The influence of silicon nanoclusters on the optical properties of a-SiNx samples: A theoretical study. Applied Physics Letters, 2012, 100, 181905.	1.5	11
44	Optical absorption modulation by selective codoping of SiGe core-shell nanowires. Journal of Applied Physics, 2012, 112, .	1.1	11
45	Second-harmonic generation in silicon waveguides strained by silicon nitride. Nature Materials, 2012, 11, 148-154.	13.3	280
46	Band structure analysis in SiGe nanowires. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 705-711.	1.7	13
47	Band-Offset Driven Efficiency of the Doping of SiGe Coreâ˜Shell Nanowires. Nano Letters, 2011, 11, 594-598.	4.5	63
48	Auger recombination in Si and GaAs semiconductors:Ab initioresults. Physical Review B, 2011, 84, .	1.1	36
49	Local-field effects in silicon nanoclusters. Physical Review B, 2011, 84, .	1.1	17
50	Self-energy and excitonic effects in the electronic and optical properties of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>TiO</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msu phases. Physical Review B, 2010, 82, .	1.1	236
51	Silicon and Germanium Nanostructures for Photovoltaic Applications: Ab-Initio Results. Nanoscale Research Letters, 2010, 5, 1637-1649.	3.1	41
52	Electronic and optical properties of Si and Ge nanocrystals: An ab initio study. Superlattices and Microstructures, 2010, 47, 178-181.	1.4	1
53	Localâ€fields and disorder effects in freeâ€standing and embedded Si nanocrystallites. Physica Status Solidi (B): Basic Research, 2010, 247, 2113-2117.	0.7	9
54	Segregation, quantum confinement effect and band offset for [110] SiGe NWs. Physica Status Solidi (B): Basic Research, 2010, 247, 2096-2101.	0.7	16

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55	Manyâ€body effects on the electronic and optical properties of Si nanowires from ab initio approaches. Physica Status Solidi (B): Basic Research, 2010, 247, 2089-2095.	0.7	7
56	Giant excitonic exchange splitting in Si nanowires: First-principles calculations. Physical Review B, 2010, 81, .	1.1	19
57	Ab initiooptoelectronic properties of SiGe nanowires: Role of many-body effects. Physical Review B, 2010, 82, .	1.1	22
58	High luminescence in smallSi/SiO2nanocrystals: A theoretical study. Physical Review B, 2010, 81, .	1.1	51
59	SiGe nanowires: Structural stability, quantum confinement, and electronic properties. Physical Review B, 2009, 80, .	1.1	47
60	The Role of the Surface Coverage on the Structural and the Electronic Properties of TiO2 Nanocrystals. Materials Research Society Symposia Proceedings, 2009, 1178, 114.	0.1	0
61	Electronic properties and dielectric response of surfaces and nanowires of silicon from ab-initio approaches. Superlattices and Microstructures, 2009, 46, 234-239.	1.4	5
62	Optical properties of silicon nanocrystallites in SiO2 matrix: Crystalline vs. amorphous case. Superlattices and Microstructures, 2009, 46, 246-252.	1.4	20
63	Effects of simultaneous doping with boron and phosphorous on the structural, electronic and optical properties of silicon nanostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 939-946.	1.3	35
64	Impurity screening in silicon nanocrystals. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 966-968.	1.3	2
65	Ab-initio calculations of luminescence and optical gain properties in silicon nanostructures. Comptes Rendus Physique, 2009, 10, 575-586.	0.3	28
66	Silicon nanocrystallites in a<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>SiO</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>matrix: Role of disorder and size. Physical Review B, 2009, 79, .	1.1	57
67	Size, oxidation, and strain in small<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>Si</mml:mtext><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mtext>SiO</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>nanocrystals. Physical Review B, 2009, 80, .	1.1	63
68	Engineering Quantum Confined Silicon Nanostructures: Ab-Initio Study of the Structural, Electronic and Optical Properties. Advances in Quantum Chemistry, 2009, 58, 203-279.	0.4	11
69	Reduced quantum confinement effect and electron-hole separation in SiGe nanowires. Physical Review B, 2009, 79, .	1.1	48
70	Novel optoelectronic properties of simultaneously n- and p-doped silicon nanostructures. Superlattices and Microstructures, 2008, 44, 337-347.	1.4	26
71	Oxygen vacancy effects on the Schottky barrier height at the Au/TiO2(110) interface: A first principle study. Solid State Communications, 2008, 147, 205-207.	0.9	35
72	Optical absorption spectra of doped and codoped Si nanocrystallites. Physical Review B, 2008, 78, .	1.1	31

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73	Structural, electronic, and surface properties of anatase<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>TiO</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> from first principles. Physical Review B, 2008, 78, .	1.1	56
74	First-Principles Study of Silicon Nanocrystals: Structural and Electronic Properties, Absorption, Emission, and Doping. Journal of Nanoscience and Nanotechnology, 2008, 8, 479-492.	0.9	25
75	Structural features and electronic properties of group-III-, group-IV-, and group-V-doped Si nanocrystallites. Journal of Physics Condensed Matter, 2007, 19, 466211.	0.7	37
76	Excitons in silicon nanocrystallites: The nature of luminescence. Physical Review B, 2007, 75, .	1.1	57
77	Engineering silicon nanocrystals: Theoretical study of the effect of codoping with boron and phosphorus. Physical Review B, 2007, 76, .	1.1	81
78	From Si Nanowires to Porous Silicon: The Role of Excitonic Effects. Physical Review Letters, 2007, 98, 036807.	2.9	151
79	Codoping goes Nano: Structural and Optical Properties of Boron and Phosphorus Codoped Silicon Nanocrystals. AIP Conference Proceedings, 2007, , .	0.3	0
80	Ab-initio electronic and optical properties of low dimensional systems: From single particle to many-body approaches. Surface Science, 2007, 601, 2696-2701.	0.8	6
81	Doping in silicon nanocrystals. Surface Science, 2007, 601, 2724-2729.	0.8	11
82	Doping in silicon nanostructures. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 1312-1317.	0.8	11
83	First-principles optical properties of silicon and germanium nanowires. Surface Science, 2007, 601, 2707-2711.	0.8	58
84	Screening in semiconductor nanocrystals:Ab initioresults and Thomas-Fermi theory. Physical Review B, 2006, 73, .	1.1	34
85	Thomas-Fermi model of electronic screening in semiconductor nanocrystals. Europhysics Letters, 2006, 74, 519-525.	0.7	21
86	Understanding Doping In Silicon Nanostructures. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1585-1591.	1.9	32
87	Doping in silicon nanocrystals: An ab initio study of the structural, electronic and optical properties. Journal of Luminescence, 2006, 121, 335-339.	1.5	30
88	The electronic and optical properties of silicon nanoclusters: absorption and emission. Optical Materials, 2005, 27, 1008-1013.	1.7	28
89	Ab initiostudy on oxidized silicon clusters and silicon nanocrystals embedded inSiO2: Beyond the quantum confinement effect. Physical Review B, 2005, 71, .	1.1	143
90	Electronic, structural and optical properties of hydrogenated silicon nanocrystals: the role of the excited states. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 3263-3267.	0.8	2

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91	Formation energies of silicon nanocrystals: role of dimension and passivation. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 3354-3358.	0.8	5
92	Ab-initio Calculations Of The Electronic Properties of Silicon Nanocrystals: Absorption, Emission, Stokes Shift. AIP Conference Proceedings, 2005, , .	0.3	0
93	Excitons in germanium nanowires: Quantum confinement, orientation, and anisotropy effects within a first-principles approach. Physical Review B, 2005, 72, .	1.1	93
94	Simultaneously B- and P-doped silicon nanoclusters: Formation energies and electronic properties. Applied Physics Letters, 2005, 87, 173120.	1.5	95
95	First-principles study ofn- andp-doped silicon nanoclusters. Physical Review B, 2005, 72, .	1.1	188
96	Ab initiostructural and electronic properties of hydrogenated silicon nanoclusters in the ground and excited state. Physical Review B, 2004, 69, .	1.1	117
97	Orientation effects in the electronic and optical properties of germanium quantum wires. Physical Review B, 2004, 70, .	1.1	38
98	Semiclassical and Quantum Transport in Si/SiO2Superlattices. Journal of Computational Electronics, 2003, 2, 417-422.	1.3	0
99	Optical properties of Ge and Si nanosheetsâ€“â€“confinement and symmetry effects. Surface Science, 2003, 527, 30-40.	0.8	13
100	Oxygen role on the optoelectronic properties of silicon nanodots. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 101, 34-38.	1.7	7
101	Monte Carlo analysis of electron heating in Si/SiO2 superlattices. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 455-460.	1.3	2
102	Oxygen role on the structural and optoelectronic properties of silicon nanodots. Physica Status Solidi A, 2003, 197, 251-256.	1.7	24
103	Silicon Nanostructures: Wells, Wires, and Dots. Springer Tracts in Modern Physics, 2003, , 123-178.	0.1	5
104	Role of the interface region on the optoelectronic properties of silicon nanocrystals embedded inSiO2. Physical Review B, 2003, 68, .	1.1	235
105	Multiple Si=O bonds at the silicon cluster surface. Journal of Applied Physics, 2003, 94, 2130-2132.	1.1	75
106	Dynamics of stimulated emission in silicon nanocrystals. Applied Physics Letters, 2003, 82, 4636-4638.	1.5	151
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110	Monte Carlo simulation of electron transport inSi/SiO2superlattices: Vertical transport enhanced by a parallel field. Physical Review B, 2002, 66, .	1.1	6
111	True direct gap absorption in germanium quantum films. Physical Review B, 2002, 65, .	1.1	12
112	Monte Carlo simulation of electron transport in Si/SiO 2 superlattices. , 2002, , .		0
113	Isolated and Embedded Silicon Based Nanodots: the Role of Surface Oxygen. Materials Research Society Symposia Proceedings, 2002, 737, 17.	0.1	0
114	Si nanostructures embedded in SiO 2 : electronic and optical properties. , 2002, 4808, 73.		3
115	Effect of oxygen on the optical properties of small silicon pyramidal clusters. Physical Review B, 2002, 65, .	1.1	45
116	The electronic and optical properties of InGaAs/InP and InAlAs/InP superlattices. Surface Science, 2001, 489, 59-71.	0.8	7
117	Structural and Optical Properties of Silicon Nanocrystals Grown by Plasma-Enhanced Chemical Vapor Deposition. Journal of Nanoscience and Nanotechnology, 2001, 1, 159-168.	0.9	26
118	First-principles electronic structure of rare-earth arsenides. European Physical Journal B, 2001, 23, 191-199.	0.6	10
119	Role of defects in Si/SiO2 quantum wells. Optical Materials, 2001, 17, 95-98.	1.7	11
120	In-plane anisotropy of the optical properties of(In0.5Ga0.5As)n/(InP)nsuperlattices. Physical Review B, 2001, 63, .	1.1	7
121	Relation between the in-plane polarization anisotropy of the optical properties and the microscopic atomic configuration in (Ga0.5In0.5As)/(InP) superlattices. Springer Proceedings in Physics, 2001, , 477-478.	0.1	0
122	From Undulating Si Quantum Wires to Si Quantum Dots: A Model for Porous Silicon. Physica Status Solidi A, 2000, 182, 301-306.	1.7	10
123	Symmetry and passivation dependence of the optical properties of nanocrystalline silicon structures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 69-70, 444-448.	1.7	6
124	Porous silicon: a quantum sponge structure for silicon based optoelectronics. Surface Science Reports, 2000, 38, 1-126.	3.8	1,256
125	The electronic and optical properties of Si/SiO2 superlattices: role of confined and defect states. Surface Science, 2000, 470, 32-42.	0.8	60
126	First Principles Optical Properties of Low Dimensional Silicon Structures. , 2000, , 147-160.		0

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127	Optical properties of Si/CaF2 superlattices. Journal of Luminescence, 1998, 80, 411-415.	1.5	3
128	Optical Properties of Confined Si Structures. Physica Status Solidi A, 1998, 170, 377-390.	1.7	27
129	First-principles optical properties ofSi/CaF2multiple quantum wells. Physical Review B, 1998, 57, 14776-14782.	1.1	23
130	Role of symmetry reduction in the polarization dependence of the optical absorption in non-common-atom superlattices. Physical Review B, 1998, 58, R1742-R1745.	1.1	18
131	Optical properties of isolated and interacting silicon quantum wires. Thin Solid Films, 1997, 297, 154-162.	0.8	35
132	Optical emission from small Si particles. Solid State Communications, 1997, 102, 545-549.	0.9	69
133	Si/CaF 2 superlattices: a silicon light-emitting nanostructure. , 1996, 2777, 27.		0
134	Ab-Initio Calculation of the Optical Properties of Silicon Quantum Wires. Materials Research Society Symposia Proceedings, 1996, 452, 63.	0.1	0
135	The luminescence transition in porous silicon: the nature of the electronic states. Thin Solid Films, 1996, 276, 261-264.	0.8	2
136	The optical transition in porous Si: The effects of quantum confinement, surface states and hydrogen passivation. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1996, 18, 1121-1129.	0.4	1
137	Electronic structure of rare earth arsenide/gallium arsenide superlattices. Solid State Communications, 1996, 100, 477-480.	0.9	7
138	Auger lineshape analysis of porous silicon: experiment and theory. Thin Solid Films, 1996, 276, 244-247.	0.8	13
139	Luminescence in porous silicon: the role of confinement and passivation. Applied Surface Science, 1996, 102, 395-398.	3.1	12
140	Electron states and luminescence transition in porous silicon. Physical Review B, 1996, 53, 4557-4564.	1.1	41
141	Electronic structure of the 1Ã—1YBa2Cu3O7/PrBa2Cu3O7superlattice: A local-spin-density approximation with on-site Coulomb interaction. Physical Review B, 1996, 54, 1404-1409.	1.1	7
142	Si/CaF2 Superlattices. A Direct Gap Structure Due to Interface State Coupling. Physica Status Solidi (B): Basic Research, 1995, 190, 117-122.	0.7	9
143	Electronic structure ofPrBa2Cu3O7: A local-spin-density approximation with on-site Coulomb interaction. Physical Review B, 1995, 52, 10468-10473.	1.1	18
144	Light Emission at Room Temperature from Si/CaF ₂ Multilayers. Europhysics Letters, 1995, 31, 25-30.	0.7	43

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145	Hole Filling and Interlayer Coupling in YBa 2 Cu 3 O 7 /PrBa 2 Cu 3 O 7 Superlattices. Europhysics Letters, 1995, 31, 317-322.	0.7	7
146	Quasiparticle Band Structure of NiO: The Mott-Hubbard Picture Regained. Physical Review Letters, 1994, 73, 3129-3132.	2.9	67
147	Electronic structure of thin Si layers in CaF2: Hybridization versus confinement. Solid-State Electronics, 1994, 37, 1145-1147.	0.8	0
148	Gap opening in ultrathin Si layers: Role of confined and interface states. Physical Review Letters, 1994, 72, 1044-1047.	2.9	31
149	First-principles investigation of the electronic structure of Si-based layered structures. Surface Science, 1994, 307-309, 984-988.	0.8	2
150	Electronic Properties of Low Dimensional Silicon Structures. , 1993, , 219-228.		2
151	The electronic properties of the CaF2î—¸Si(111) system: from monolayer coverage to solid-solid interface. Surface Science, 1992, 269-270, 743-747.	0.8	14
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153	Fermi-level pinning and interface states at Pbî—¸Si(111) interface. Solid State Communications, 1992, 82, 863-866.	0.9	2
154	Theoretical approaches to the Schottky barrier problem. Applied Surface Science, 1992, 56-58, 290-300.	3.1	8
155	Initial formation of the CaF2 interface: a theoretical study. Surface Science, 1991, 251-252, 462-466.	0.8	4
156	Chemical bond and electronic states at theCaF2-Si(111) and Ca-Si(111) interfaces. Physical Review B, 1991, 43, 9823-9830.	1.1	37
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158	The electronic properties of SiNiSi2(111) epitaxial interfaces. Vacuum, 1990, 41, 681-683.	1.6	2
159	Covalency in the adsorption of Na on Si(111). Physical Review B, 1990, 42, 7671-7674.	1.1	34
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161	Selfconsistent LMTO calculation for semiconductor clean surfaces. Surface Science, 1989, 211-212, 572-577.	0.8	15
162	Image potential at metal surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1987, 5, 727-730.	0.9	6

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163	The Electronic Properties of Silicon-Silicide Epitaxial Interfaces. Materials Research Society Symposia Proceedings, 1987, 102, 315.	0.1	2
164	First principle investigation of the electronic properties of silicon-silicide interfaces. Surface Science, 1987, 189-190, 285-293.	0.8	20
165	Electron density profiles at charged metal surfaces in the weighted density approximation. Surface Science, 1987, 189-190, 776-781.	0.8	22
166	Image-force effects on the barrier height for metal-metal tunneling electrons. Physical Review B, 1987, 35, 848-850.	1.1	11
167	Image Plane for Surface Potential. Europhysics Letters, 1986, 1, 661-667.	0.7	76
168	Non-local exchange and correlation in the jellium model of surfaces. Surface Science, 1986, 178, 244-255.	0.8	25
169	Interaction potential between rare-gas atoms and metal surfaces. Physical Review B, 1986, 33, 873-878.	1.1	18
170	The Heâ^—(1s, 2s) + Ne interaction potential. Physics Letters, Section A: General, Atomic and Solid State Physics, 1985, 110, 451-452.	0.9	1
171	Self-trapped exciton bubble size growth in solid neon. Journal of Physics and Chemistry of Solids, 1985, 46, 123-126.	1.9	8
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174	Density-functional calculation of atomic structure with nonlocal exchange and correlation. Physical Review A, 1985, 31, 3550-3556.	1.0	25
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